

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

2SK4098FS — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- · High-speed switching.
- · Avalanche resistance guarantee.
- · 10V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	7	Α
	IDpack *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	28	Α
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	33	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		98	mJ
Avalanche Current *5	I _{AV}		6	Α

Note: *1 Shows chip capability.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Marking: K4098FS

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^{*2} Package limited.

^{*3} SANYO's condition is radiation from backside.

^{*4} VDD=50V, L=5mH, IAV=6A

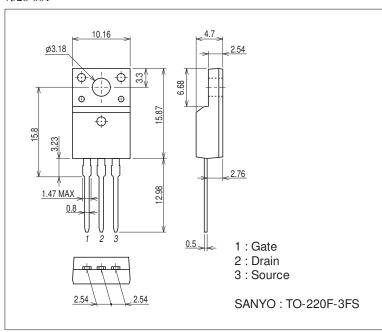
^{*5} L≤5mH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =480V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =3.5A	2.1	4.2		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =3.5A, V _G S=10V		0.9	1.1	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		600		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		120		pF
Reverse Transfer Capacitance	Crss	V _{DS} =30V, f=1MHz		25		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		17		ns
Rise Time	t _r	See specified Test Circuit.		34		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		80		ns
Fall Time	tf	See specified Test Circuit.		30		ns
Total Gate Charge	Qg	V _{DS} =200V, V _{GS} =10V, I _D =7A		23.5		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =7A		4.5		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =200V, V _{GS} =10V, I _D =7A		13.5		nC
Diode Forward Voltage	V _{SD}	I _S =7A, V _{GS} =0V		0.9	1.2	V

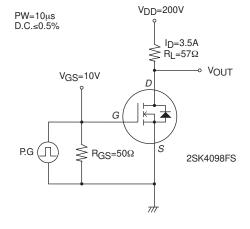
Package Dimensions

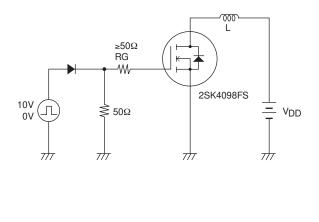
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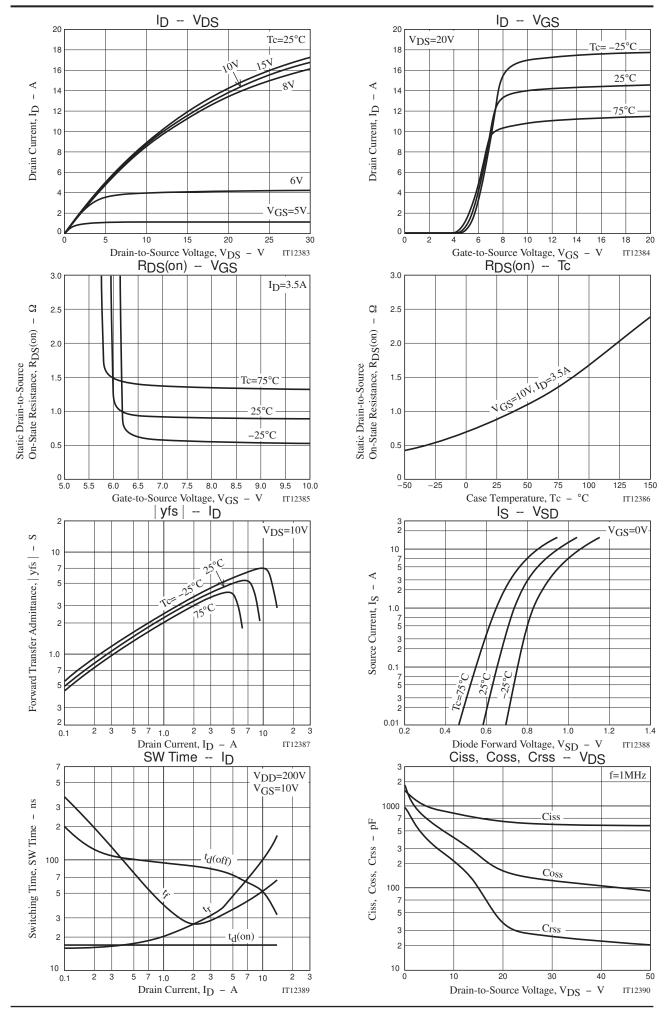


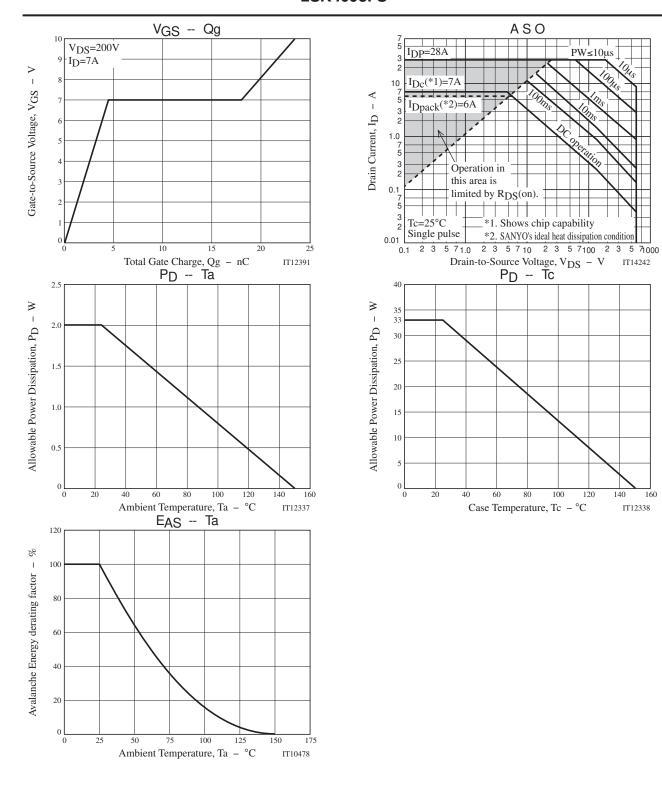
Switching Time Test Circuit

Avalanche Resistance Test Circuit









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Note on usage: Since the 2SK4098FS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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